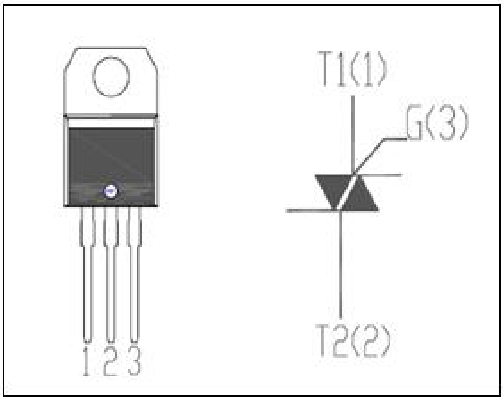
isc 1991

INCHANGE SEMICONDUCTOR

isc Thyristors T1635T-8T

DESCRIPTION

- With TO-220 packaging
- Operating in 3 quadrants
- High commutation capability
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- Solid state relays;heating and cooking appliances
- Switching applications

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER		MAX	UNIT
V_{DRM}	Repetitive peak off-state voltage		800	V
V_{RRM}	Repetitive peak reverse voltage		800	V
$I_{T(RSM)}$	Average on-state current @Tc=15℃		16	A
I_{TSM}	Surge non-repetitive on-state current	50HZ 60HZ	120 126	A
$P_{G(AV)}$	Average gate power dissipation (over any 20 ms period)		1.0	W
T_j	Operating junction temperature		-40~150	℃
T_{stg}	Storage temperature		-40~150	℃

ELECTRICAL CHARACTERISTICS (T_C=25℃ unless otherwise specified)

SYMBOL	PARAMETER	CONDITIONS		MIN	MAX	UNIT
I_{RRM}	Repetitive peak reverse current	$V_R=V_{RRM}$ Rated; $V_D=V_{DRM}$ Rated;	Tj=25℃ Tj=125℃ Tj=150℃		0.008 1.0 3.0	mA
I_{DRM}	Repetitive peak off-state current					
V_{TM}	On-state voltage	I_T=22.6A			1.55	V
I_{GT}	Gate-trigger current	V_D =12V;RG=30Ω	I	1.75	35	mA
			II	1.75	35	
			III	1.75	35	
V_{GT}	Gate-trigger voltage	V_D =12V;RG=30Ω			1.3	V
Rth (j-c)	Junction to case	Half cycle			1.1	℃/W

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